

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Atty. Docket

ROBERTUS D.J. VERHAAR ET AL

NL 000627

Serial No.

Group Art Unit

Filed: CONCURRENTLY

Ex.

Title: METHOD OF FORMING A SEMICONDUCOTR STRUCTURE

Commissioner for Patents  
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Sir:

Prior to calculation of the filing fee and examination, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend the claims as follows:

3. (amended) A method as claimed in claim 1, wherein a non-volatile memory cell is applied as part of the semiconductor structure, which non-volatile memory cell employs the ONO insulating layer between a floating gate and control gate thereof.

5. (amended) A method as claimed in claim 1, wherein the subsequent oxidation of the silicon sub-layer of the Oxide-Nitride-

Silicon insulating layer takes place also to provide a high voltage oxide layer for a peripheral structure.

6. (amended) A method as claimed in claim 1, wherein the silicon layer is re-oxidized into a thermal oxide.

REMARKS

The foregoing amendments to the claims were made solely to avoid filing the claims in the multiple dependent form so as to avoid the additional filing fee.

The claims were not amended in order to address issues of patentability and Applicants respectfully reserve all rights they may have under the Doctrine of Equivalents. Applicants furthermore reserve their right to reintroduce subject matter deleted herein at a later time during the prosecution of this application or continuing applications.

Respectfully submitted,

By   
Michael E. Marion, Reg. 32,266  
Attorney  
(914) 333-9641

APPENDIX

3. (amended) A method as claimed in claim 1-~~or 2~~, wherein a non-volatile memory cell is applied as part of the semiconductor structure, which non-volatile memory cell employs the ONO insulating layer between a floating gate and control gate thereof.

5. (amended) A method as claimed in claim 1, 2, 3 or 4, wherein the subsequent oxidation of the silicon sub-layer of the Oxide-Nitride-Silicon insulating layer takes place also to provide a high voltage oxide layer for a peripheral structure.

6. (amended) A method as claimed in ~~any one of claims 1 to 5~~claim 1, wherein the silicon layer is re-oxidized into a thermal oxide.

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